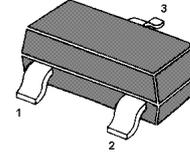


PNP Silicon Epitaxial Planar Transistor

For switching and general purpose applications.

The transistor is subdivided into three groups P, Q and R, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	32	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_{amb}=25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=3\text{V}$, $-I_C=100\text{mA}$					
Current Gain Group P	h_{FE}	82	-	180	-
Current Gain Group Q	h_{FE}	120	-	270	-
Current Gain Group R	h_{FE}	180	-	390	-
Collector-base breakdown voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V
Collector-emitter breakdown voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	32	-	-	V
Emitter-base breakdown voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $-V_{CB}=20\text{V}$	$-I_{CBO}$	-	-	1	μA
Emitter Cutoff Current at $-V_{EB}=4\text{V}$	$-I_{EBO}$	-	-	1	μA
Collector Saturation Voltage at $-I_C=300\text{mA}$, $-I_B=30\text{mA}$	$-V_{CE(sat)}$	-	-	0.6	V
Transition Frequency at $-V_{CE}=5\text{V}$, $-I_E=20\text{mA}$, $f=100\text{MHz}$	f_T	-	200	-	MHz
Collector Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{ob}	-	7	-	pF

Typical Characteristics

